

# Maurice S Skolnick

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

613  
papers

20,790  
citations

72  
h-index

119  
g-index

676  
ext. papers

22,791  
ext. citations

4.4  
avg, IF

6.16  
L-index

#	Paper	IF	Citations
613	Engineering Chiral Light-Matter Interactions in a Waveguide-Coupled Nanocavity.. <i>ACS Photonics</i> , <b>2022</b> , 9, 706-713	6.3	0
612	Condensation of 2D exciton-polaritons in an open-access microcavity. <i>Journal of Applied Physics</i> , <b>2022</b> , 131, 093101	2.5	0
611	Exciton-polaritons in GaAs-based slab waveguide photonic crystals. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 181101	3.4	1
610	Ultrafast-nonlinear ultraviolet pulse modulation in an AlInGaN polariton waveguide operating up to room temperature. <i>Nature Communications</i> , <b>2021</b> , 12, 3504	17.4	3
609	Experimental observation of topological Z exciton-polaritons in transition metal dichalcogenide monolayers. <i>Nature Communications</i> , <b>2021</b> , 12, 4425	17.4	12
608	Optical analogue of Dresselhaus spin-orbit interaction in photonic graphene. <i>Nature Photonics</i> , <b>2021</b> , 15, 193-196	33.9	8
607	Strong coupling of excitons in 2D MoSe <sub>2</sub> /hBN heterostructure with optical bound states in the continuum. <i>Journal of Physics: Conference Series</i> , <b>2020</b> , 1461, 012012	0.3	1
606	A semiconductor topological photonic ring resonator. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 061102	3.4	15
605	Chiral topological photonics with an embedded quantum emitter. <i>Optica</i> , <b>2020</b> , 7, 1690	8.6	20
604	Highly nonlinear trion-polaritons in a monolayer semiconductor. <i>Nature Communications</i> , <b>2020</b> , 11, 3589	17.4	38
603	Photon Statistics of Filtered Resonance Fluorescence. <i>Physical Review Letters</i> , <b>2020</b> , 125, 043603	7.4	5
602	Nonlinear polaritons in a monolayer semiconductor coupled to optical bound states in the continuum. <i>Light: Science and Applications</i> , <b>2020</b> , 9, 56	16.7	55
601	Tunable Photon Statistics Exploiting the Fano Effect in a Waveguide. <i>Physical Review Letters</i> , <b>2019</b> , 122, 173603	7.4	14
600	Complete characterization of GaAs gradient-elastic tensors and reconstruction of internal strain in GaAs/AlGaAs quantum dots using nuclear magnetic resonance. <i>Physical Review B</i> , <b>2019</b> , 99,	3.3	1
599	Direct Measurement of Hyperfine Shifts and Radio Frequency Manipulation of Nuclear Spins in Individual CdTe/ZnTe Quantum Dots. <i>Physical Review Letters</i> , <b>2019</b> , 122, 096801	7.4	5
598	Effect of photonic spin-orbit coupling on the topological edge modes of a Su-Schrieffer-Heeger chain. <i>Physical Review B</i> , <b>2019</b> , 99,	3.3	23
597	Pulse control protocols for preserving coherence in dipolar-coupled nuclear spin baths. <i>Nature Communications</i> , <b>2019</b> , 10, 3157	17.4	8

596	Light Scattering from Solid-State Quantum Emitters: Beyond the Atomic Picture. <i>Physical Review Letters</i> , <b>2019</b> , 123, 167403	7.4	20
595	Measurement of local optomechanical properties of a direct bandgap 2D semiconductor. <i>APL Materials</i> , <b>2019</b> , 7, 101126	5.7	10
594	Amplification of nonlinear polariton pulses in waveguides. <i>Optics Express</i> , <b>2019</b> , 27, 10692-10704	3.3	1
593	Spatiotemporal continuum generation in polariton waveguides. <i>Light: Science and Applications</i> , <b>2019</b> , 8, 6	16.7	7
592	Exciton Polaritons in a Two-Dimensional Lieb Lattice with Spin-Orbit Coupling. <i>Physical Review Letters</i> , <b>2018</b> , 120, 097401	7.4	82
591	Transition from Propagating Polariton Solitons to a Standing Wave Condensate Induced by Interactions. <i>Physical Review Letters</i> , <b>2018</b> , 120, 167402	7.4	6
590	Quantum fluids of light in acoustic lattices. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 033001	3	3
589	Electrical control of nonlinear quantum optics in a nano-photonics waveguide. <i>Optica</i> , <b>2018</b> , 5, 644	8.6	15
588	Electro-mechanical control of an on-chip optical beam splitter containing an embedded quantum emitter. <i>Optics Letters</i> , <b>2018</b> , 43, 2142-2145	3	9
587	High Purcell factor generation of indistinguishable on-chip single photons. <i>Nature Nanotechnology</i> , <b>2018</b> , 13, 835-840	28.7	105
586	Formation of a macroscopically occupied polariton state in a tunable open-access microcavity under resonant excitation. <i>Journal of Applied Physics</i> , <b>2018</b> , 124, 025703	2.5	3
585	Nonreciprocal Transmission and Reflection of a Chirally Coupled Quantum Dot. <i>Nano Letters</i> , <b>2018</b> , 18, 5475-5481	11.5	10
584	Cross calibration of deformation potentials and gradient-elastic tensors of GaAs using photoluminescence and nuclear magnetic resonance spectroscopy in GaAs/AlGaAs quantum dot structures. <i>Physical Review B</i> , <b>2018</b> , 97,	3.3	6
583	Valley coherent exciton-polaritons in a monolayer semiconductor. <i>Nature Communications</i> , <b>2018</b> , 9, 4797	17.4	37
582	Spin Domains in One-Dimensional Conservative Polariton Solitons. <i>ACS Photonics</i> , <b>2018</b> , 5, 5095-5102	6.3	10
581	Polarization-resolved strong light-matter coupling in planar GaAs/AlGaAs waveguides. <i>Optics Letters</i> , <b>2018</b> , 43, 4526	3	8
580	Path-dependent initialization of a single quantum dot exciton spin in a nanophotonic waveguide. <i>Physical Review B</i> , <b>2017</b> , 95,	3.3	15
579	Dark Solitons in High Velocity Waveguide Polariton Fluids. <i>Physical Review Letters</i> , <b>2017</b> , 119, 097403	7.4	47

578	Valley-addressable polaritons in atomically thin semiconductors. <i>Nature Photonics</i> , <b>2017</b> , 11, 497-501	33.9	127
577	Measurement of the spin temperature of optically cooled nuclei and GaAs hyperfine constants in GaAs/AlGaAs quantum dots. <i>Nature Materials</i> , <b>2017</b> , 16, 982-986	27	26
576	Backward Cherenkov radiation emitted by polariton solitons in a microcavity wire. <i>Nature Communications</i> , <b>2017</b> , 8, 1554	17.4	18
575	Metalorganic vapor phase epitaxy growth, transmission electron microscopy, and magneto-optical spectroscopy of individual InAs <sub>x</sub> P <sub>1-x</sub> /Ga <sub>0.5</sub> In <sub>0.5</sub> P quantum dots. <i>Physical Review Materials</i> , <b>2017</b> , 1,	3.2	1
574	Dynamic vibronic coupling in InGaAs quantum dots [Invited]. <i>Journal of the Optical Society of America B: Optical Physics</i> , <b>2016</b> , 33, C115	1.7	9
573	Ultrafast depopulation of a quantum dot by LA-phonon-assisted stimulated emission. <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	13
572	Vanishing electron g factor and long-lived nuclear spin polarization in weakly strained nanohole-filled GaAs/AlGaAs quantum dots. <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	18
571	Tuning Nonlinear Mechanical Mode Coupling in GaAs Nanowires Using Cross-Section Morphology Control. <i>Nano Letters</i> , <b>2016</b> , 16, 7414-7420	11.5	10
570	Chirality of nanophotonic waveguide with embedded quantum emitter for unidirectional spin transfer. <i>Nature Communications</i> , <b>2016</b> , 7, 11183	17.4	158
569	Full Stark control of polariton states on a spin-orbit hypersphere. <i>Physical Review B</i> , <b>2016</b> , 94,	3.3	5
568	Few-second-long correlation times in a quantum dot nuclear spin bath probed by frequency-comb nuclear magnetic resonance spectroscopy. <i>Nature Physics</i> , <b>2016</b> , 12, 688-693	16.2	12
567	On-chip interference of single photons from an embedded quantum dot and an external laser. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 251101	3.4	16
566	Single-photon electroluminescence for on-chip quantum networks. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 161101	3.4	10
565	Design and characterization of high optical quality InGaAs/GaAs/AlGaAs-based polariton microcavities. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 021109	3.4	7
564	Suppression of nuclear spin bath fluctuations in self-assembled quantum dots induced by inhomogeneous strain. <i>Nature Communications</i> , <b>2015</b> , 6, 6348	17.4	36
563	Phonon-assisted population inversion of a single InGaAs/GaAs quantum dot by pulsed laser excitation. <i>Physical Review Letters</i> , <b>2015</b> , 114, 137401	7.4	96
562	Ultra-low-power hybrid light-matter solitons. <i>Nature Communications</i> , <b>2015</b> , 6, 8317	17.4	62
561	Exciton-polaritons in van der Waals heterostructures embedded in tunable microcavities. <i>Nature Communications</i> , <b>2015</b> , 6, 8579	17.4	275

560	High-fidelity initialization of long-lived quantum dot hole spin qubits by reduced fine-structure splitting. <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	17
559	Logic gates with bright dissipative polariton solitons in Bragg cavity systems. <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	16
558	Spin Textures of Exciton-Polaritons in a Tunable Microcavity with Large TE-TM Splitting. <i>Physical Review Letters</i> , <b>2015</b> , 115, 246401	7.4	54
557	Tunable polaritonic molecules in an open microcavity system. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 201106	3.4	18
556	On-chip electrically controlled routing of photons from a single quantum dot. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 221101	3.4	17
555	Spatial Patterns of Dissipative Polariton Solitons in Semiconductor Microcavities. <i>Physical Review Letters</i> , <b>2015</b> , 115, 256401	7.4	17
554	Linearly polarized emission from an embedded quantum dot using nanowire morphology control. <i>Nano Letters</i> , <b>2015</b> , 15, 1559-63	11.5	30
553	Two-dimensional metal-chalcogenide films in tunable optical microcavities. <i>Nano Letters</i> , <b>2014</b> , 14, 7003-8	11.5	109
552	Waveguide coupled resonance fluorescence from on-chip quantum emitter. <i>Nano Letters</i> , <b>2014</b> , 14, 6997-7002	11.5	57
551	Effects of spin-dependent interactions on polarization of bright polariton solitons. <i>Physical Review Letters</i> , <b>2014</b> , 112, 046403	7.4	44
550	Waveguide-coupled photonic crystal cavity for quantum dot spin readout. <i>Optics Express</i> , <b>2014</b> , 22, 2376-85	3.5	16
549	Strong exciton-photon coupling in open semiconductor microcavities. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 192107	3.4	40
548	Monolithic integration of a quantum emitter with a compact on-chip beam-splitter. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 231107	3.4	41
547	Exciton-polariton gap solitons in two-dimensional lattices. <i>Physical Review Letters</i> , <b>2013</b> , 111, 146401	7.4	108
546	Element-sensitive measurement of the hole nuclear spin interaction in quantum dots. <i>Nature Physics</i> , <b>2013</b> , 9, 74-78	16.2	61
545	Asymmetry tuning of Fano resonances in GaAs photonic crystal cavities. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 111112	3.4	9
544	Spontaneous vortices in optically shaped potential profiles in semiconductor microcavities. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	10
543	Exciton polaritons in semiconductor waveguides. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 012109	3.4	40

542	Homogeneous array of nanowire-embedded quantum light emitters. <i>Nano Letters</i> , <b>2013</b> , 13, 861-5	11.5	33
541	Enhanced photocurrent readout for a quantum dot qubit by bias modulation. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 181108	3.4	4
540	III-V quantum light source and cavity-QED on silicon. <i>Scientific Reports</i> , <b>2013</b> , 3, 1239	4.9	27
539	Dynamic nuclear polarization in InGaAs/GaAs and GaAs/AlGaAs quantum dots under nonresonant ultralow-power optical excitation. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	12
538	Optical control of the emission direction of a quantum dot. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 241102	3.4	21
537	Effect of polariton-polariton interactions on the excitation spectrum of a nonequilibrium condensate in a periodic potential. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	27
536	Interfacing spins in an InGaAs quantum dot to a semiconductor waveguide circuit using emitted photons. <i>Physical Review Letters</i> , <b>2013</b> , 110, 037402	7.4	91
535	Observation of bright polariton solitons in a semiconductor microcavity. <i>Nature Photonics</i> , <b>2012</b> , 6, 50-55	33.9	204
534	Coherent optical control of the spin of a single hole in an InAs/GaAs quantum dot. <i>Physical Review Letters</i> , <b>2012</b> , 108, 017402	7.4	90
533	Structural analysis of strained quantum dots using nuclear magnetic resonance. <i>Nature Nanotechnology</i> , <b>2012</b> , 7, 646-50	28.7	52
532	Effect of a GaAsP shell on the optical properties of self-catalyzed GaAs nanowires grown on silicon. <i>Nano Letters</i> , <b>2012</b> , 12, 5269-74	11.5	28
531	Coexisting Polariton Condensates and Their Temporal Coherence in Semiconductor Microcavities. <i>Springer Series in Solid-state Sciences</i> , <b>2012</b> , 147-171	0.4	
530	Dynamic exciton-polariton macroscopic coherent phases in a tunable dot lattice. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	17
529	Wavefunction of polariton condensates in a tunable acoustic lattice. <i>New Journal of Physics</i> , <b>2012</b> , 14, 075011	2.9	9
528	Restoring mode degeneracy in H1 photonic crystal cavities by uniaxial strain tuning. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 121116	3.4	37
527	Disorder-limited photon propagation and Anderson-localization in photonic crystal waveguides. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 051116	3.4	12
526	Fast preparation of a single-hole spin in an InAs/GaAs quantum dot in a Voigt-geometry magnetic field. <i>Physical Review B</i> , <b>2012</b> , 85,	3.3	34
525	Polarization-resolved resonant fluorescence of a single semiconductor quantum dot. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 251118	3.4	

524	Solitons in semiconductor microcavities. <i>Nature Photonics</i> , <b>2012</b> , 6, 204-204	33.9	3
523	Exciton-Polariton Coupling with Acoustic Phonons. <i>Springer Series in Solid-state Sciences</i> , <b>2012</b> , 289-306	0.4	
522	Direct measurement of the hole-nuclear spin interaction in single InP/GaInP quantum dots using photoluminescence spectroscopy. <i>Physical Review Letters</i> , <b>2011</b> , 106, 027402	7.4	84
521	Mode structure of coupled L3 photonic crystal cavities. <i>Optics Express</i> , <b>2011</b> , 19, 5670-5	3.3	45
520	Charge control in InP/(Ga,In)P single quantum dots embedded in Schottky diodes. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	8
519	Fano Resonance in GaAs 2D Photonic Crystal Nanocavities <b>2011</b> ,		1
518	Fast control of nuclear spin polarization in an optically pumped single quantum dot. <i>Nature Materials</i> , <b>2011</b> , 10, 844-8	27	27
517	Effects of the piezoelectric field on the modulation of exciton-polaritons by surface acoustic waves. <i>Superlattices and Microstructures</i> , <b>2011</b> , 49, 233-240	2.8	13
516	Light-polarization-independent nuclear spin alignment in a quantum dot. <i>Physical Review B</i> , <b>2011</b> , 83,	3.3	11
515	Suppression of Zeeman splitting of the energy levels of exciton-polariton condensates in semiconductor microcavities in an external magnetic field. <i>Physical Review Letters</i> , <b>2011</b> , 106, 257401	7.4	45
514	Unpolarized H1 photonic crystal nanocavities fabricated by stretched lattice design. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 041101	3.4	16
513	Stark spectroscopy and radiative lifetimes in single self-assembled CdTe quantum dots. <i>Physical Review B</i> , <b>2011</b> , 83,	3.3	15
512	Effect of detuning on the phonon induced dephasing of optically driven InGaAs/GaAs quantum dots. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 102415	2.5	16
511	Persistent currents and quantized vortices in a polariton superfluid. <i>Nature Physics</i> , <b>2010</b> , 6, 527-533	16.2	223
510	Polariton condensation in dynamic acoustic lattices. <i>Physical Review Letters</i> , <b>2010</b> , 105, 116402	7.4	152
509	Pumping of nuclear spins by optical excitation of spin-forbidden transitions in a quantum dot. <i>Physical Review Letters</i> , <b>2010</b> , 104, 066804	7.4	53
508	Control of spontaneous emission from InP single quantum dots in GaInP photonic crystal nanocavities. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 181104	3.4	13
507	Dynamics of optically induced nuclear spin polarization in individual InP/GaxIn <sub>1-x</sub> P quantum dots. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	26

506	Fast high fidelity hole spin initialization in a single InGaAs quantum dot. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 061113	3-4	28
505	Polarization bistability and resultant spin rings in semiconductor microcavities. <i>Physical Review Letters</i> , <b>2010</b> , 105, 216402	7-4	68
504	Phonon-induced Rabi-frequency renormalization of optically driven single InGaAs/GaAs quantum dots. <i>Physical Review Letters</i> , <b>2010</b> , 105, 177402	7-4	152
503	Damping of exciton Rabi rotations by acoustic phonons in optically excited InGaAs/GaAs quantum dots. <i>Physical Review Letters</i> , <b>2010</b> , 104, 017402	7-4	219
502	Splitting and lasing of whispering gallery modes in quantum dot micropillars. <i>Optics Express</i> , <b>2010</b> , 18, 22578-92	3-3	16
501	Effect of interactions on vortices in a nonequilibrium polariton condensate. <i>Physical Review Letters</i> , <b>2010</b> , 104, 126402	7-4	52
500	Optically tunable nuclear magnetic resonance in a single quantum dot. <i>Physical Review B</i> , <b>2010</b> , 82,	3-3	19
499	Superfluidity in polariton condensates. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 210, 012060	0-3	1
498	Inversion recovery measurements of exciton fine-structure beats in a single quantum dot. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 245, 012010	0-3	2
497	Growth of low density InP/GaNp quantum dots. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 245, 012061	0-3	3
496	Optimization of low density InP/GaNp quantum dots for single-dot studies. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 245, 012093	0-3	1
495	Quantum key distribution system in standard telecommunications fiber using a short wavelength single photon source. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 073102	2-5	12
494	Two-color two-photon Rabi oscillation of biexciton in single InAs/GaAs quantum dot. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 2485-2488	3	10
493	One dimensional confinement of microcavity polaritons using non-piezoelectric surface acoustic waves. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 2548-2551	3	5
492	Voltage-controlled nuclear polarization switching in a single InxGa1-xAs quantum dot. <i>Physical Review B</i> , <b>2009</b> , 79,	3-3	5
491	Coexisting nonequilibrium condensates with long-range spatial coherence in semiconductor microcavities. <i>Physical Review B</i> , <b>2009</b> , 80,	3-3	63
490	Beating of exciton-dressed states in a single semiconductor InGaAs/GaAs quantum dot. <i>Physical Review Letters</i> , <b>2009</b> , 102, 207401	7-4	38
489	Suppression of nuclear spin diffusion at a GaAs/AlxGa1-xAs interface measured with a single quantum-dot nanoprobe. <i>Physical Review B</i> , <b>2009</b> , 79,	3-3	24



488	Voltage-controlled motional narrowing in a semiconductor quantum dot. <i>New Journal of Physics</i> , <b>2009</b> , 11, 093032	2.9	2
487	Two-colour photocurrent detection technique for coherent control of a single InGaAs/GaAs quantum dot. <i>Physica Status Solidi (B): Basic Research</i> , <b>2009</b> , 246, 824-827	1.3	1
486	Collective fluid dynamics of a polariton condensate in a semiconductor microcavity. <i>Nature</i> , <b>2009</b> , 457, 291-5	50.4	429
485	Long lifetimes of quantum-dot intersublevel transitions in the terahertz range. <i>Nature Materials</i> , <b>2009</b> , 8, 803-7	27	137
484	Towards coherent optical control of a single hole spin: Rabi rotation of a trion conditional on the spin state of the hole. <i>Solid State Communications</i> , <b>2009</b> , 149, 1458-1465	1.6	2
483	Ultrafast all-optical switching in AlGaAs photonic crystal waveguide interferometers. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 141108	3.4	14
482	Enhanced room-temperature quantum-dot effects in modulation-doped InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 171902	3.4	13
481	Quantum dot dipole orientation and excitation efficiency of micropillar modes. <i>Optics Express</i> , <b>2008</b> , 16, 19201-7	3.3	4
480	Self-organization of multiple polariton-polariton scattering in semiconductor microcavities. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	51
479	Long nuclear spin polarization decay times controlled by optical pumping in individual quantum dots. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	23
478	Two-qubit conditional quantum-logic operation in a single self-assembled quantum dot. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	49
477	Intersublevel polaron dephasing in self-assembled quantum dots. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	19
476	Enhanced nonradiative Auger recombination in p-type modulation doped InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 101903	3.4	17
475	Carrier lifetimes in type-II InAs quantum dots capped with a GaAsSb strain reducing layer. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 251905	3.4	37
474	Nuclear spin pumping under resonant optical excitation in a quantum dot. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 073113	3.4	13
473	Overhauser effect in individual InP <sub>x</sub> In <sub>1-x</sub> P dots. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	26
472	Fast optical preparation, control, and readout of a single quantum dot spin. <i>Physical Review Letters</i> , <b>2008</b> , 100, 197401	7.4	120
471	Intrinsic decoherence mechanisms in the microcavity polariton condensate. <i>Physical Review Letters</i> , <b>2008</b> , 101, 067404	7.4	123

470	Excitonic spin lifetimes in InGaN quantum wells and epilayers. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 053523	2.3	2
469	Exciton warming in III-V semiconductors and microcavities. <i>Superlattices and Microstructures</i> , <b>2008</b> , 43, 449-453	2.8	
468	Ultrafast tailoring of the exciton distribution in quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , <b>2008</b> , 245, 1064-1066	1.3	1
467	Spatial distribution of strong and weak coupled exciton-polaritons in semiconductor microcavities. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 2049-2052	3	1
466	Electroluminescence emission from polariton states in GaAs-based semiconductor microcavities. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 061107	3.4	62
465	Investigating the Capping of InAs Quantum Dots by InGaAs. <i>Springer Proceedings in Physics</i> , <b>2008</b> , 259-262	2.2	3
464	Mode structure of the L3 photonic crystal cavity. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 241117	3.4	85
463	Single photon sources based upon single quantum dots in semiconductor microcavity pillars. <i>Journal of Modern Optics</i> , <b>2007</b> , 54, 453-465	1.1	15
462	Phonon satellites and time-resolved studies of carrier recombination dynamics in InGaN quantum wells. <i>Superlattices and Microstructures</i> , <b>2007</b> , 41, 419-424	2.8	6
461	Spin-dependent coexistence of weakly coupled and strongly coupled modes in semiconductor microcavities. <i>Superlattices and Microstructures</i> , <b>2007</b> , 41, 321-327	2.8	
460	Band gap dependence of the recombination processes in InAs/GaAs quantum dots studied using hydrostatic pressure. <i>Physica Status Solidi (B): Basic Research</i> , <b>2007</b> , 244, 82-86	1.3	5
459	Temperature dependent polariton emission from strongly coupled organic semiconductor microcavities. <i>Superlattices and Microstructures</i> , <b>2007</b> , 41, 289-292	2.8	13
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25	Electron-Hole Liquid in Ge in High Magnetic Field. <i>Springer Series in Solid-state Sciences</i> , <b>1981</b> , 208-215	0.4	
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19	Properties of the electron-hole liquid in GaP. <i>Physical Review B</i> , <b>1979</b> , 19, 2231-2245	3.3	37
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17	The electron-hole-liquid in 15R-SiC. <i>Solid State Communications</i> , <b>1978</b> , 28, 865-868	1.6	7
16	Investigation of the optical absorption of Fe <sub>3</sub> BO <sub>6</sub> after oxygen annealing and under the influence of strong magnetic fields. <i>Journal of Applied Physics</i> , <b>1978</b> , 49, 2200-2202	2.5	7
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11	A high-precision study of excited-state transitions of shallow donors in semiconductors. <i>Journal of the Optical Society of America</i> , <b>1977</b> , 67, 947		17
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8	An investigation of the anisotropy of the valence band of GaAs by cyclotron resonance. <i>Journal of Physics C: Solid State Physics</i> , <b>1976</b> , 9, 2809-2821		85
7	Cyclotron resonance measurements of the non-parabolicity of the conduction bands in silicon and germanium. <i>Journal of Physics C: Solid State Physics</i> , <b>1976</b> , 9, 2803-2808		19
6	Submillimetre cyclotron resonance of electrons in GaP. <i>Solid State Communications</i> , <b>1975</b> , 16, 363-366	1.6	33
5	Hole mass measurement in p-type InP and GaP by submillimetre cyclotron resonance in pulsed magnetic fields. <i>Solid State Communications</i> , <b>1974</b> , 15, 693-697	1.6	69
4	Far infrared photoconductivity from majority and minority impurities in high purity Si and Ge. <i>Solid State Communications</i> , <b>1974</b> , 15, 1403-1408	1.6	70
3	Effect of annealing on anticorrelated InGaAs/GaAs quantum dots	255-258	

2 Microstructural studies of InAs/GaAs self-assembled quantum dots grown by selective area molecular beam epitaxy 267-270

1 Vortices in Resonant Polariton Condensates in Semiconductor Microcavities 424-444